

Aluminum Nitride (AlN)

Features

- High Thermal Conductivity
- Thermal Expansion Coefficient Close to That of Si
- High Resistivity
- Low Dielectric Constant and Loss
- Inert to Almost All Molten Metals
- Excellent Mechanical Strength

Applications

- Circuit Substrates for Semiconductor Module and IC
- Heat Sink Materials for Power Transistors, Thyristors, LDs and LEDs etc.
- Crucibles for Molten Metal and Preparing Single Crystals
- Window Material for Infrared ray and Radar

Characteristics of Material

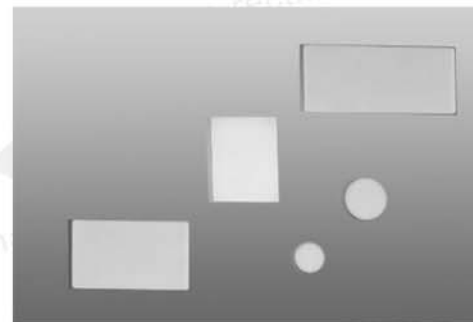
Item	Unit	Value
Bulk Density	g/cm ³	3.24~3.3
Thermal Expansion Coefficient	10 ⁻⁶ /°C	4.36 (at 20~400°C)
Modulus of Elasticity	GPa	310
Mohs Hardness		7~8
Fracture Toughness	MPam ^{1/2}	3.2~3.35
Vickers Hardness	GPa	12
Bending Strength	MPa	>325
Thermal Conductivity	W/m.K	170~228
Dielectric Constant (at 1MHz)		8.6
Dielectric Loss Angle(at 1MHz)	× 10 ⁻⁴	5~10
Dielectric Strength	kV/mm	>15
Volume Resistivity	Ω cm	>3.6 × 10 ¹³

Metallized AlN Substrates

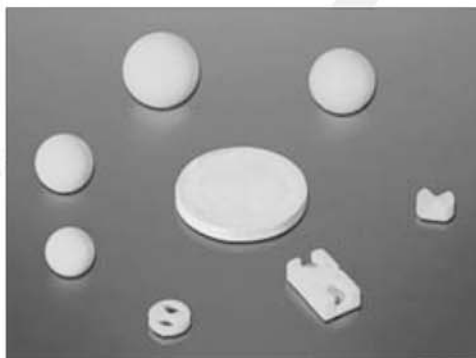
Item	Metallized Method						
	Pd-Ag	W-Mo	Mo-Mn	Pt-Ag	Ti/Cu/Ni/Au	Ta ₂ N/Ni	DCB
Material							
Feature	Thick film	Thick film	Thick film	Thick film	Thin film	Thin film	Direct Copper Bonded



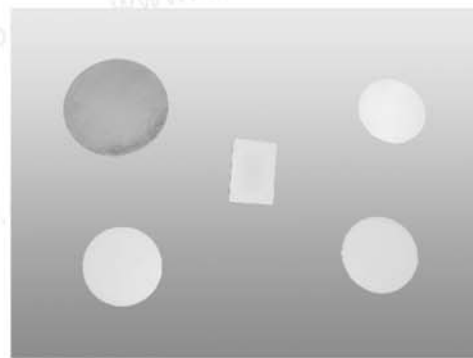
Crucible



Window materials for infrared and radar applications



Balls and parts



Plates, discs